



SPTS High Flow Plenum for Pegasus

November 2012



The information in the presentation is the property of SPTS and may not be duplicated, disclosed to any third party, or used for any purpose other than that for which it is supplied without the written consent of SPTS.

Executive Summary



- SPTS Pegasus hardware upgrades are available to improve the etch rate/scallop size relationship

- New “High Flow” Plenum Design
 - Smaller volume
 - New gas flow route

- Improves deposition step efficiency
 - Opens process window to achieve higher throughputs
 - 40% Reduction in C4F8 usage
 - 25% Reduction in overall process time

- ROI within 2 Months

High Flow Plenum



- SPTS have a new design for the source gas plenum
- Improved efficiency for gas transport
- Most notably for the deposition step
 - Deposition step time can be reduced
 - Deposition removal time can be reduced
 - Overall gas usage is reduced & net etch rates are increased

- The High Flow Plenum is a significant change to the module configuration.
- As a consequence, recipe tuning is required to reset process after installation
 - To take advantage of the improved gas behaviour
 - SPTS can offer process support when introducing high flow plenum

New Plenum Process Trials



Process Cycle Times	Standard Plenum	New Plenum	New Plenum Modified process (less deposition)
7s etch, 4s deposition			
Etch Rate	13.1 $\mu\text{m}/\text{min}$	12.9 $\mu\text{m}/\text{min}$	14.1 $\mu\text{m}/\text{min}$ (+9%)
Sidewall Scallop	>600nm	>600nm	>600nm (No Change)
1.75s etch, 1s deposition			
Etch Rate	9.9 $\mu\text{m}/\text{min}$	12.3 $\mu\text{m}/\text{min}$	13.02 $\mu\text{m}/\text{min}$ (+6%)
Sidewall Scallop	Not Measurable	154nm	117nm (-24%)

TSV Example

~40:1 Aspect Ratio



Parameter	Standard Plenum	New Plenum
Average Etch Depth	143	163
Depth Uniformity	≤±2%	≤±2%
Etch Rate	3.3μm/min	3.8μm/min (+15%)
Profile	89.7°-89.9°	89.7°-89.8°
Sidewall Scallops	≤255nm	≤200nm (-22%)

Reduced costs, Increased Throughput



- Data captured by Manufacturing user of Pegasus PM
- Comparing gas usage between standard and High Flow plenums

Date	C4F8 (litres)	SF6 (litres)	Dep Cycle time (sec)	Etch Cycle time (sec)	Total Process Time (mins)
Standard Plenum	4.63	10.60	4	7	51
HFP	2.83	10.20	1.5	6	38.3
HFP Advantage	-39%	-4%	-65%	-14%	-25%

- Major reduction in gas costs
 - C_4F_8 usage is reduced by ~40%
- With improved efficiency of dep/etch cycles, throughput is increased substantially
 - 25% reduction in process time

- Taking into account gas costs & throughput gains
- There is a 23% saving in operating costs (per wafer)
- Expected ROI within ≤ 2 months

High Flow Plenum Process



- The HFP is a significant change to the Pegasus PM
- There will be a process shift as a consequence of fitting the HFP
- SPTS HFP upgrade quotes will include...
 - Hardware parts required & associated labour
 - One week of process demonstration in the UK (Chargeable)
 - If process demo fails to produce a suitable process window, then no charge
 - On-site process support following install of HFP (Chargeable)
 - Due to open-ended nature, a per diem rate will be quoted
 - SPTS recommend minimum one week

- SPTS has introduced the High Flow Plenum for the Pegasus PM
- Aimed at improving sidewall quality and notching
 - While maintaining or improving etch rate
 - Reduced scalloping in order of 25%
- All achieved at same or higher etch rates
 - In order of 15% improvement
- Gas usage and overall throughput improved
 - Reduces gas costs
 - Contributes to overall lower CoO